

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (Ta=25°C)					電 氣 的 特 性 (Ta=25°C)										外 形	備 考	
				V _{CEO} (V)	V _{CEO} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	V _{CB} (V)	直流又はパルス h _{FE}		バイアス		h _{FE}	h _{ie}	h _{ie} *	h _{FE} *			h _{oe}
1	2	3	4	5					6		7		8				9	10		11	12

- 1** TYPE NUMBER
- 2** ORIGINAL MANUFACTURER
- 3** USES
- 4** MATERIAL AND STRUCTURE
- 5** MAXIMUM RATINGS
- 6** I_{CEO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CEO})
- 7** STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8** STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9** f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T.
- 10** C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11** OUTLINE
- 12** REMARKS

: とコンプリ : COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電気的特性 (T _a = 25°C)										外形	備考				
				V _{CB0} (V)	V _{EBO} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値		直流又はバルス h _{FE}		バイアス		h _{fe} h _{fs} *	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μU)			f _{ab} f _T * (Mc)	C _{ob} (pF)	τ _{bb'} h _{ie} (real)* (ns)	
									μA	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)										
2SC1541	東洋電具	RF. Conv. Mix Osc. AF. PA	Si. EP	40	5	150	300	125	1	24	330	3	10	6	-1		25.9k	0.8	7.7	250*	4.5	C _e τ _{bb'} 150pS	235	
" 1542	"	"	"	25	5	150	300	125	1	15	330	3	10	6	-1		25.9k	0.8	7.7	250*	4.5	C _e τ _{bb'} 150pS	235	
" 1543	"	SW. AF	"	40	5	20	150	125	1	24	220	3	10	6	-1		20k	0.585	5.8	t _{on} < 200nS, t _{off} < 300nS t _{rr} < 200nS		235		
" 1544	"	"	"	25	5	20	150	125	1	15	220	3	10	6	-1		20k	0.585	5.8	t _{on} < 200nS, t _{off} < 300nS t _{rr} < 200nS		235		
" 1545	"	RF. Conv. Mix Osc. PA	"	40	6	300	300	125	1	24	10,000	5	100	5	-10					250*	3	C _e τ _{bb'} 100pS	235	
" 1546	"	RF. Conv. Mix Osc. PA. SW	"	25	6	300	300	125	1	15	10,000	5	100	5	-10					250*	3	C _e τ _{bb'} 100pS	235	
" 1547	松下	RF	Si. P	30	3	20	150	175	1	25	100	10	2	10	-3	G _{ps} = 16 dB, NF = 4 dB (f = 800MHz, I _C = 3mA)			900*	0.8	60*	50C		
★ " 1548	東芝	PA	Si. EP	50		5 A	45W (T _c = 25°C)	175	1mA	20	50	5	1 A			P _o = 23W (f = 260MHz, V _{CC} = 20V, P _i = 4W)						213		
★ " 1549	富士通	AF	"	150	5	50	750	175	1	140	150	5	10						130*	20	70*	247		
★ " 1550	松下	PA	Si. TP	250	5	100	10W (T _c = 25°C)	150	100	250	100	50	5	30	-20					100*	3.5	15	236	
" 1551	東芝	LN	Si. EP	20	2	30	200	175	0.1	10	70	10	10	10	-10	G _{ps} = 7 dB, NF = 45dB (f = 4GHz, I _C = 5mA)			6.5GHz*	0.7	15*	237		
" 1552	"	"	"	20	3	30	250	175	0.1	10	70	10	10	10	-10	G _{ps} = 10.5dB, NF = 3.5dB (f = 2GHz, I _C = 5mA)			4.5GHz*	0.8	15*	237		
" 1553	"	"	"	20	3	30	175	175	0.1	10	100	10	5	10	-10	G _{ps} = 15dB, NF = 1.2dB (f = 500MHz, I _C = 3mA)			4.5GHz*	0.9	40*	50C		
" 1554	"	RF	"	30	3	120	1.2W (T _c = 25°C)	175	1	10	100	5	50	10	-50	G _{ps} = 12.5dB (f = 1GHz, I _C = 30mA)			4GHz*	1.7	15*	238		
" 1555	"	"	"	30	3	120	1.2W (T _c = 25°C)	175	1	10	100	5	50	10	-50	G _{ps} = 12.5dB (f = 1GHz, I _C = 30mA)			4GHz*	1.7	15*	239		
" 1556	"	"	"	30	3	120	1.2W (T _c = 25°C)	175	1	10	100	5	50	10	-30	G _{ps} = 14dB (f = 500MHz)			3.5GHz*	2	25*	85B		
" 1557	"	PA	"	40	3.5	180	3W (T _c = 25°C)	175	1	10	150	5	50	18	-50	P _o = 1.1W (f = 1GHz, V _{CC} = 18V, P _i = 0.3W)			3GHz*	2.2	10*	85B		
" 1558	"	LN	"	15	3	80	250	175	0.1	10	75	8	50	5	-30	G _{ps} = 10dB (f = 2GHz)			7GHz*	1.1	20*	237		
" 1559	"	"	"	15	3	80	400	175	0.1	10	75	3	50	5	-30	G _{ps} = 10dB (f = 2GHz)			7GHz*	1.1	20*	238		
" 1560	日電	RF	Si. E	25	3	70	580	200	1	15	70	10	20	10	-20	S _{21e} ² = 6.5dB (10V, 20mA, 2GHz)			4500*	C _{red} 0.6		306		
" 1561	富士通	PA	Si. EP	55	3.5	500	7W (T _c = 25°C)	175	100	20	50	5	200	12	200	P _o = 3W (f = 700MHz, V _{CC} = 28V, P _i = 0.5W)			1.8GHz*	4.5		246		
" 1562	"	"	"	55	3.5	1 A	12W (T _c = 25°C)	175	200	20	50	5	500	12	300	P _o = 9W (f = 700MHz, V _{CC} = 28V, P _i = 2W)			1.6GHz*	7		246		
" 1563	"	"	"	55	3.5	2 A	25W (T _c = 25°C)	175	400	20	50	5	1 A	12	500	P _o = 15W (f = 700MHz, V _{CC} = 28V, P _i = 4W)			1.2GHz*	12		246		
" 1564	"	"	"	55	3.5	4 A	40W (T _c = 25°C)	175	800	20	50	5	3 A	12	700	P _o = 30W (f = 700MHz, V _{CC} = 28V, P _i = 10W)			800*	23		246		
" 1565	松下	"	Si. P	150	5	250	10W (T _c = 90°C)	150	30	60	120	10	100	10	-50				150*	10	15	236	2SA795 とコンプ)	
★ " 1566	"	RF	Si. TP	250	5	100	4W (T _c = 25°C)	150	1mA	250	100	20	4	10	-3	35	300	0.4	2.7	100*	3.2	C _e τ _{bb'} 60pS	222	
" 1567	"	PA	Si. EP	100	5	500	1.2W	150	1	100	160	10	150	10	-50				120*	11	3.5k*	222	2SA794 とコンプ)	
" 1568	"	"	"	18	5	1 A	4W (T _c = 25°C)	150	0.1	18	200	2	500	6	-50				150*	12	3.5k*	222	2SA900 とコンプ)	
" 1569	東芝	"	Si. T	300	5	150	12.5W (T _c = 25°C)	150	1	100	40~170	10	50	10	-30				100*	5	10	268		
★ " 1570	三洋	LN	Si. EP	55	5	100	200	125	0.1	18	160~960	6	1	6	-1	NF = 1.5dB (f = 100Hz, V _{CE} = 6V, I _C = 0.1mA)			100*	3	C _e τ _{bb'} 250pS	138		